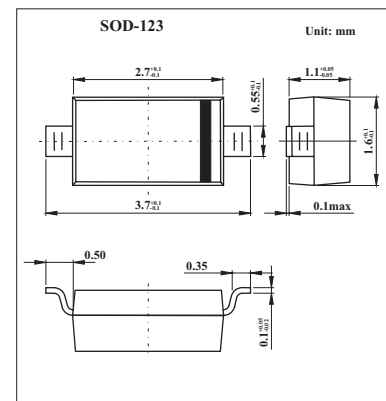


## Variable Capacitance Diode for VCXO

## HVD359

## ■ Features

- High capacitance ratio and good C-V linearity.
- To be usable at low voltage.
- Super small Flat Lead Package (SFP) is suitable for surface mount design.



## ■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Value	Unit
Reverse Voltage	V <sub>R</sub>	15	V
Junction temperature	T <sub>j</sub>	125	°C
Storage temperature	T <sub>stg</sub>	-55 to +125	°C

## ■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Conditions	Min	Max	Unit
Reverse current	I <sub>R1</sub>	V <sub>R</sub> = 10 V		10	nA
	I <sub>R2</sub>	V <sub>R</sub> = 10 V, Ta = 60°C		100	
Capacitance	C <sub>1</sub>	V <sub>R</sub> = 1 V, f = 1 MHz	24.8	29.8	pF
	C <sub>4</sub>	V <sub>R</sub> = 4 V, f = 1 MHz	6	8.3	
Capacitance ratio	n	C <sub>1</sub> / C <sub>4</sub>	3		
Series resistance	r <sub>s</sub>	V <sub>R</sub> = 4 V, f = 100 MHz		1.5	Ω
ESD-Capability *1		C = 200 pF, R = 0 Ω, Both forward and reverse direction 1 pulse.	80		V

Note:

1. Failure criterion ; I<sub>R</sub> ≥ 20 nA at V<sub>R</sub> = 10 V

## ■ Marking

Marking	G
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